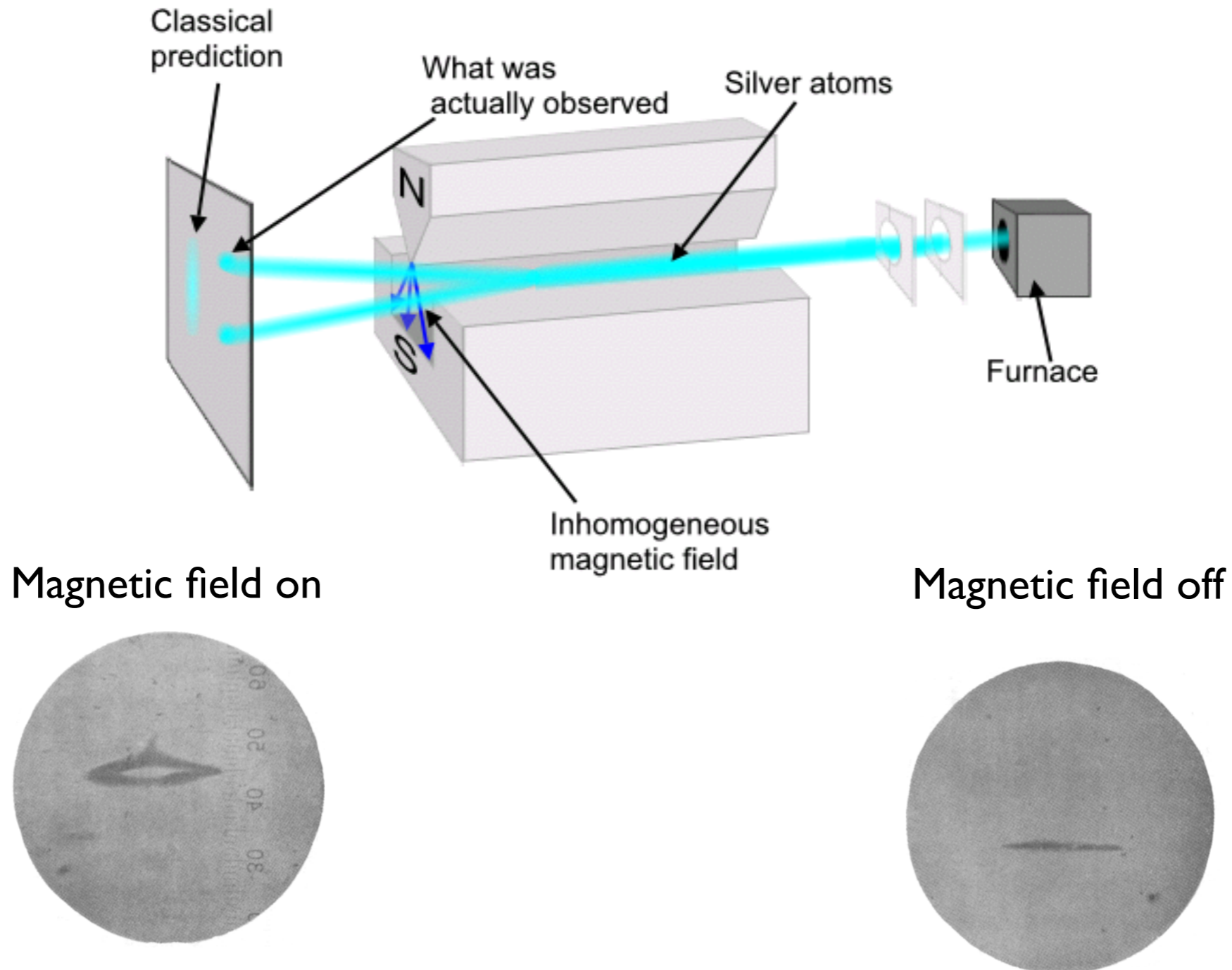


Spin in Stern-Gerlach experiment

Der experimentelle Nachweis der Richtungsquantelung im Magnetfeld.

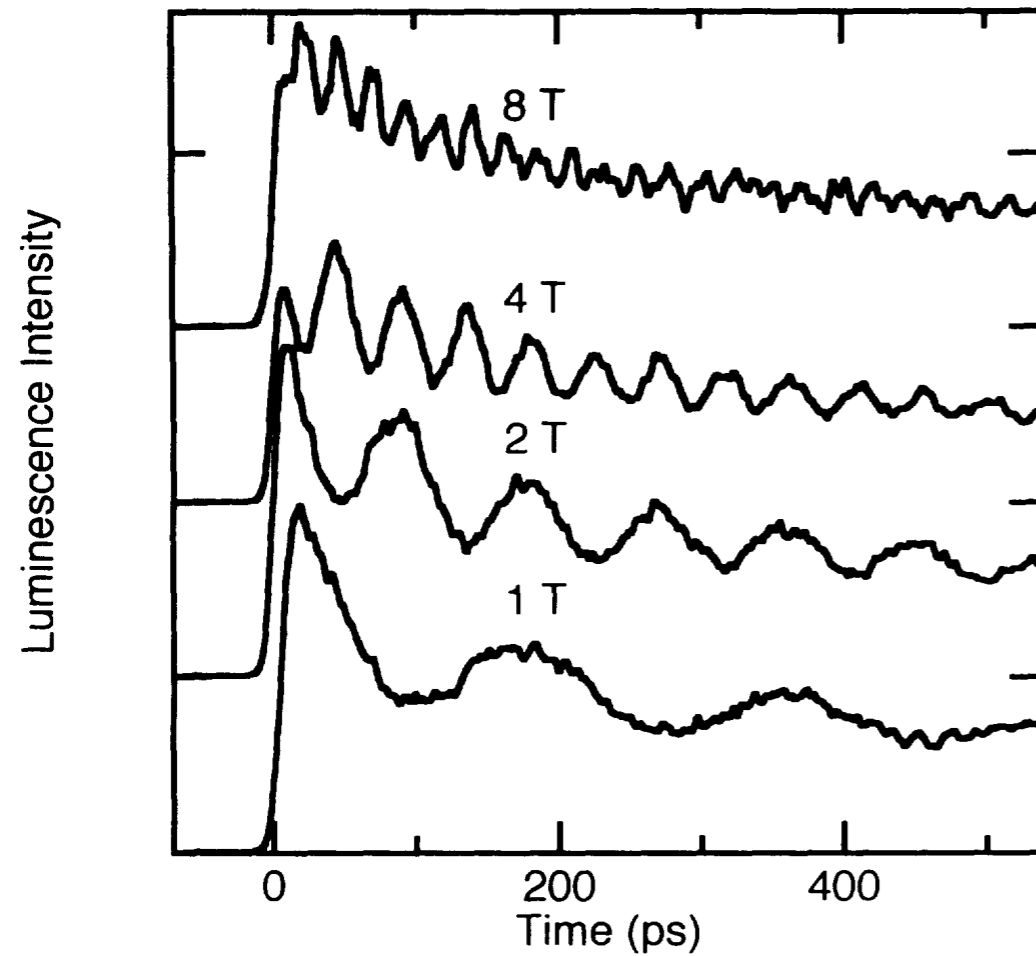
Von **Walther Gerlach** in Frankfurt a. M. und **Otto Stern** in Rostock.

Mit sieben Abbildungen. (Eingegangen am 1. März 1922.)



Spin precession in solid state devices: recombination of photo-excited spin-polarised electrons

$$\Omega_L = g\mu_B B / \hbar = eB/m \cdot g/2$$



- long spin coherence times (500 ps)
- determination of Lande g-factor (here, on a quantum well)

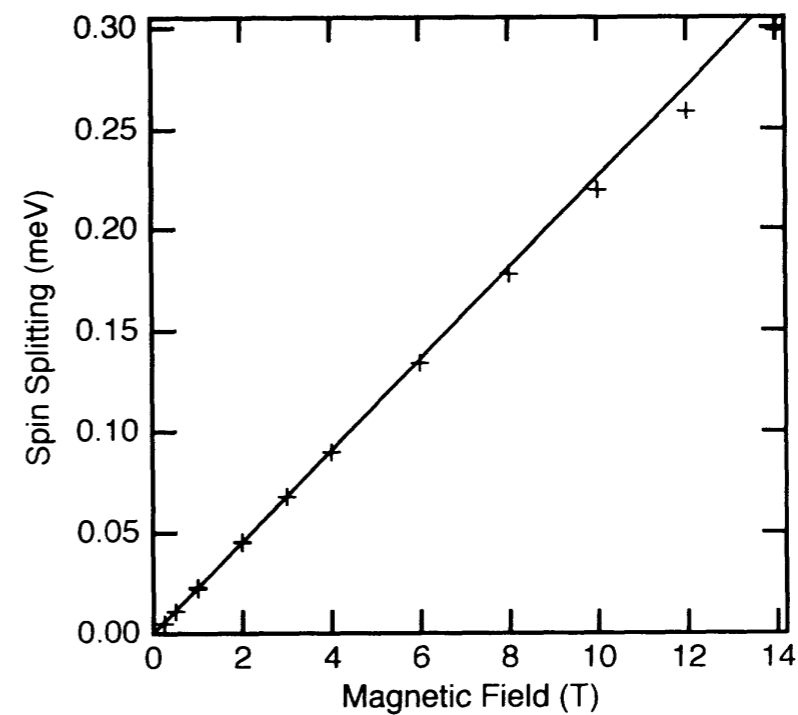
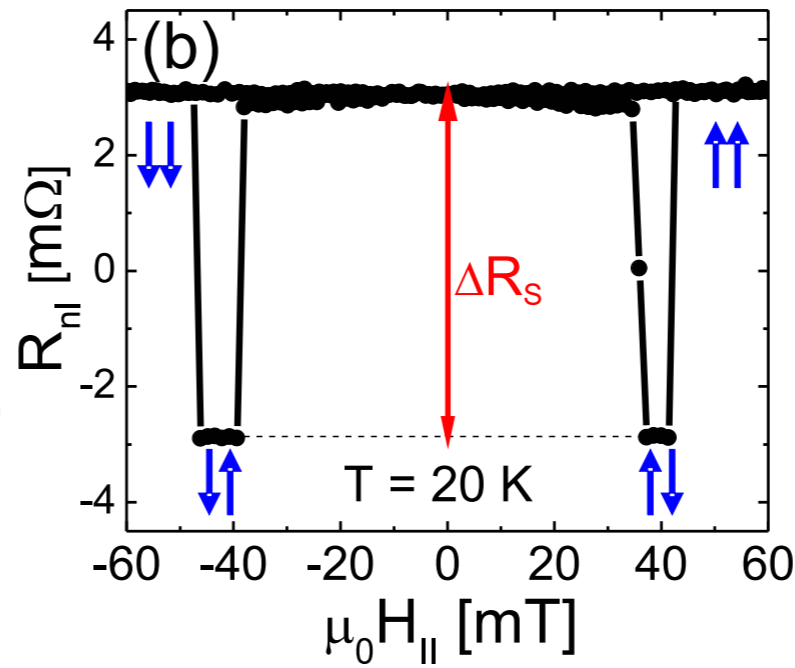
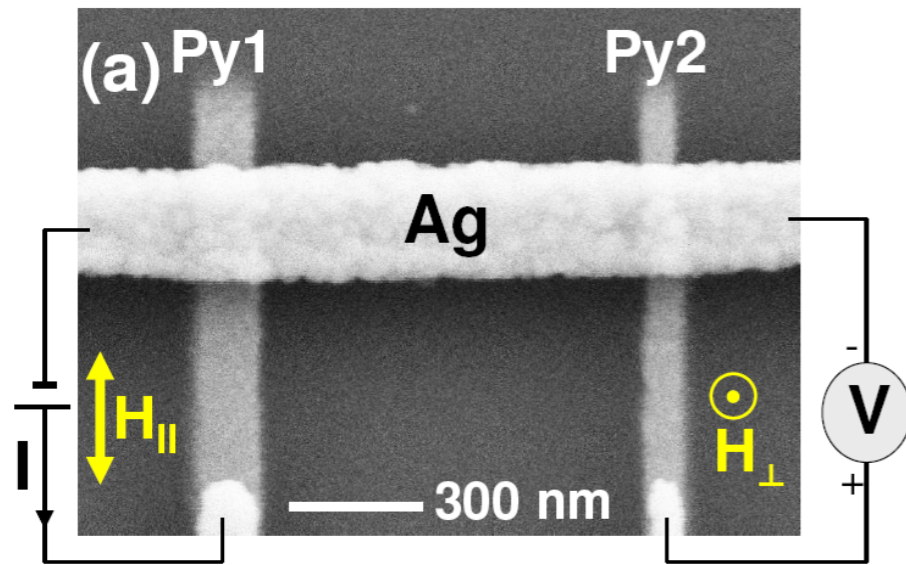


FIG. 4. Dependence of the electron spin splitting on the applied magnetic field (crosses), and spin splitting expected for a constant g factor of -0.390 (line).

Spin precession in solid state devices: Hanle effect

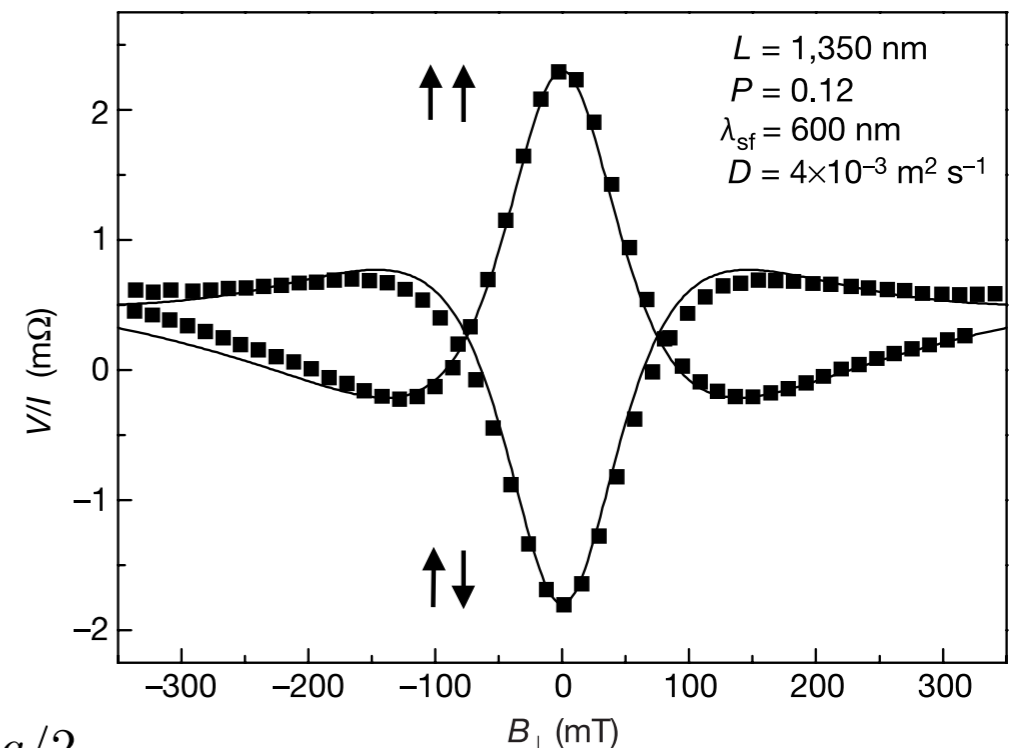


Original idea probably by Johnson & Silsbee, PRL 55, 1790 (1985)

- spin injection - left FM contact
- non-local detection on the right

$$V(B_{\perp}) = \pm I \frac{p^2}{e^2 N_{Al} A} \int_0^{\infty} P(t) \cos(\omega_L t) \exp(-t/\tau_{sf}) dt$$

$$P(t) = \frac{1}{\sqrt{4\pi Dt}} \exp[-L^2/4Dt] \quad \Omega_L = g\mu_B B/\hbar = eB/m \cdot g/2$$

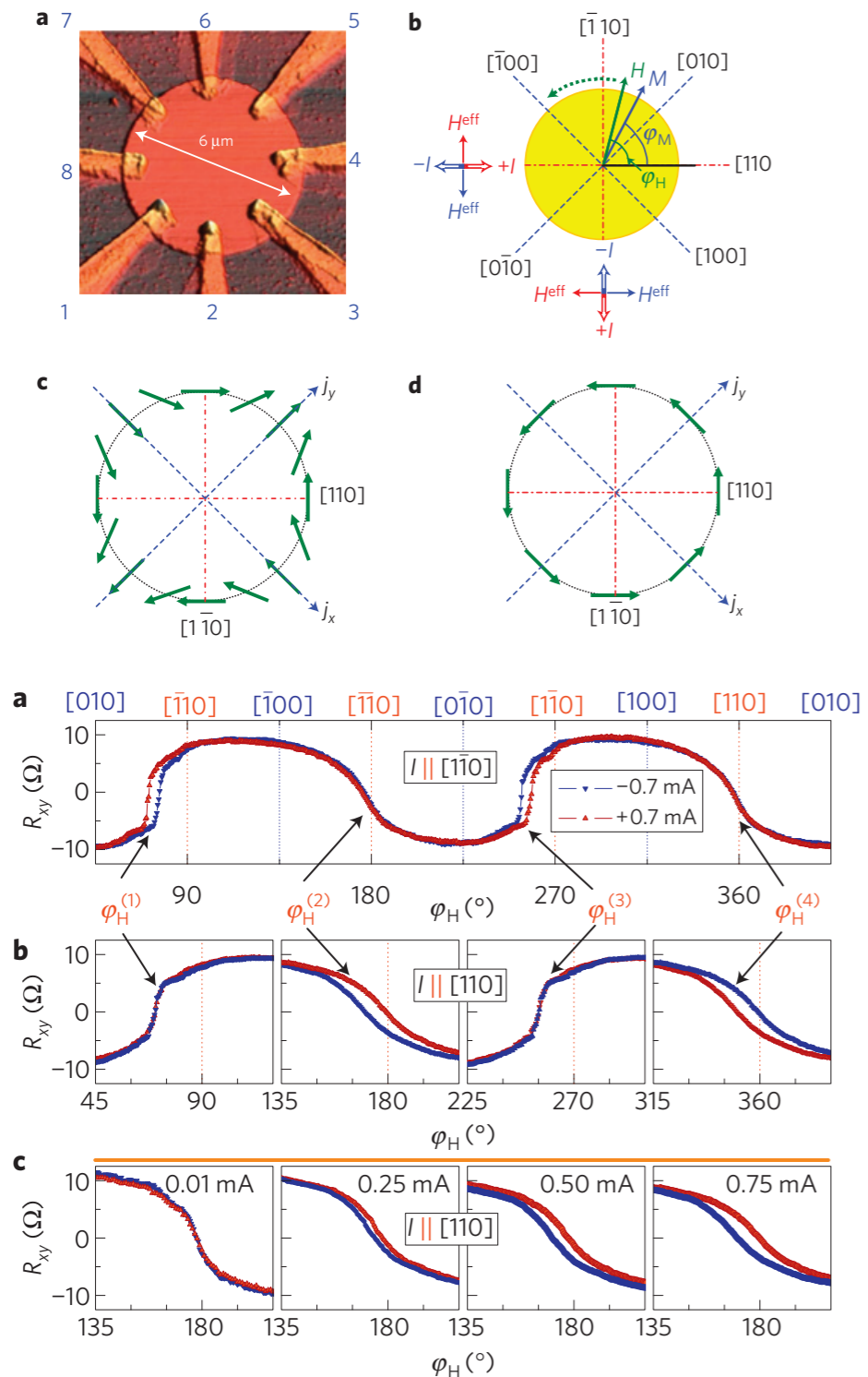


Spin polarisation in response to el. field: Edelstein effect

- ferromagnetic film
- magnetic field rotated in-plane
- “usual” response (t-AMR):

$$R_{xy} = R_0 C_I \sin 2\phi_H$$

- deviations due to magnetic anisotropy
- moreover, hysteresis...



Spin polarisation in response to el. field: Edelstein effect

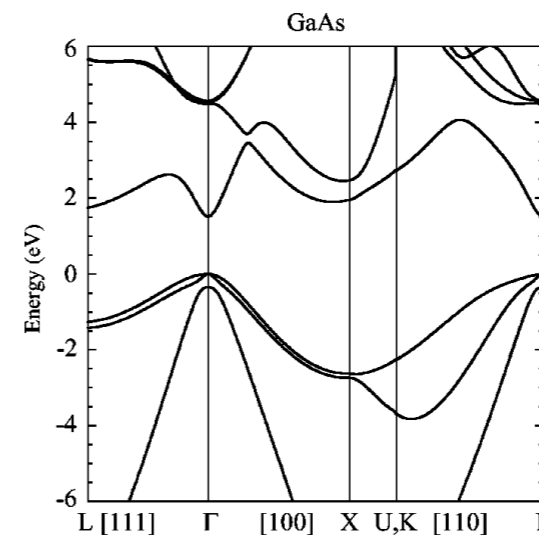
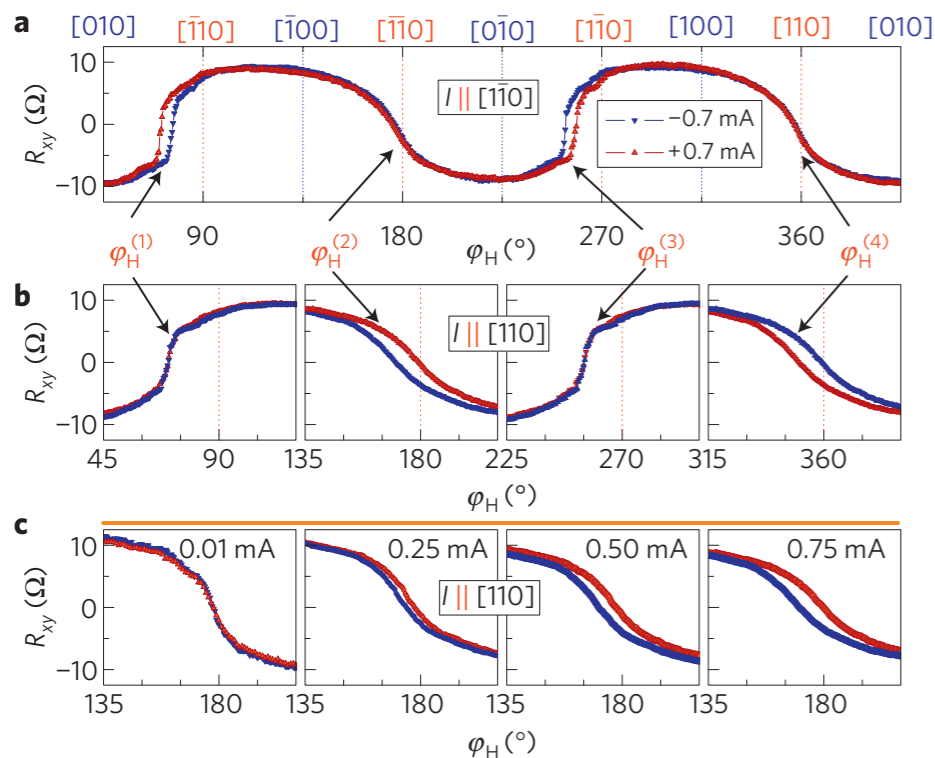
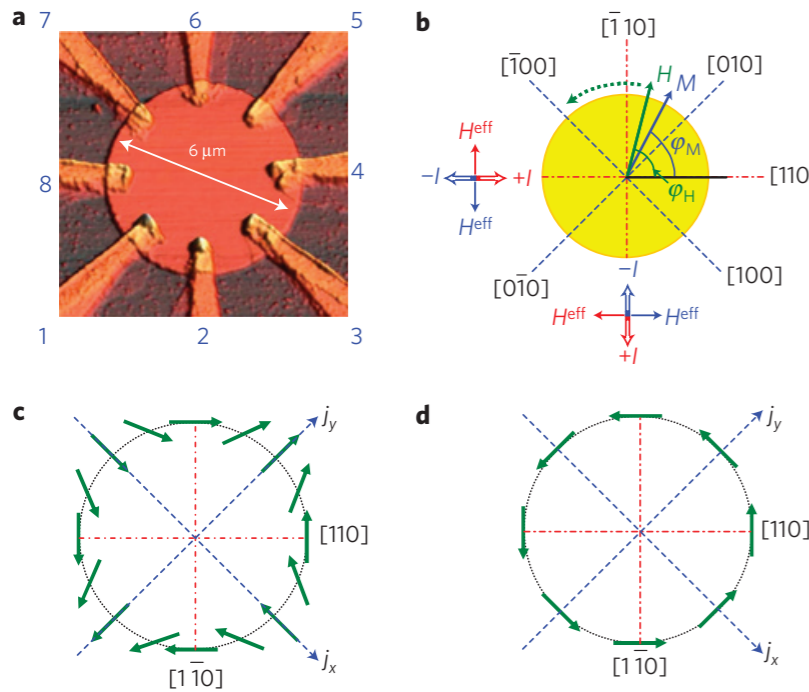
... action on magnetic moments

$$\vec{T} = \frac{J_{ex}}{\hbar} \vec{m} \times \vec{M}$$

in the context of s-d type Hamiltonian

$$H = H_{KL} + h \hat{e}_M \cdot \mathbf{s}$$

... as applicable to (Ga,Mn)As



- ferromagnetism ind. by carriers
- Mn d-states coupled to hole p-states (carrier)

$$H = H_{KL} + J_{pd} \sum_{i,I} \vec{S}_I \cdot \vec{s}_i \delta(\vec{r}_i - \vec{R}_I)$$

Topics for the bonus lecture (role of spin in transport):

- multilayers (GMR, TMR...)
- SOI-related effects:
 - ◆ Edelstein effect, SOT
 - ◆ AMR (and AHE)
 - ◆ SHE, QSHE (topological insulators)

Abbreviations explained: giant/tunneling magnetoresistance (GMR/TMR), spin-orbit interaction (SOI), anomalous Hall effect (AHE), anisotropic magnetoresistance (AMR) and (quantum) spin-Hall effect (Q)SHE.